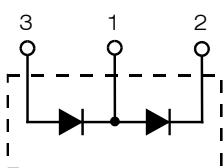


Diode Modules

PSKD 95

Preliminary Data Sheet

V_{RSM}	V_{RRM}	Type
V	V	
900	800	PSKD 95/08
1300	1200	PSKD 95/12
1500	1400	PSKD 95/14
1700	1600	PSKD 95/16
1900	1800	PSKD 95/18



I_{FRMS} = 2x 180 A
I_{FAVM} = 2x 120 A
V_{RRM} = 800-1800 V



Symbol	Test Conditions		Maximum Ratings	
I _{FRMS}	T _{VJ} = T _{VJM}		180	A
I _{FAVM}	T _C = 105°C; 180° sine		120	A
I _{FSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	2800	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	3300	A
J _{i²dt}	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	2500	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	2750	A
J _{i²dt}	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	39 200	A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	45 000	A ² s
T _{VJ}			-40...+150	°C
T _{VJM}			150	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS	t = 1 min	3000	V~
	I _{ISOL} ≤ 1 mA	t = 1 s	3600	V~
M _d	Mounting torque (M5)		2.5-4/22-35	Nm/lb.in.
	Terminal connection torque (M5)		2.5-4/22-35	Nm/lb.in.
Weight	Typical including screws		90	g

Symbol	Test Conditions		Characteristic Values	
I _R	T _{VJ} = T _{VJM} ; V _R = V _{RRM}		15	mA
V _F	I _F = 300 A; T _{VJ} = 25°C		1.43	V
V _{T0}	For power-loss calculations only		0.75	V
r _T	T _{VJ} = T _{VJM}		1.95	mΩ
Q _S	T _{VJ} = 125°C; I _F = 50 A, -di/dt = 6 A/μs		170	μC
I _{RM}			45	A
R _{thJC}	per diode; DC current		0.26	K/W
	per module		0.13	K/W
R _{thJK}	per diode; DC current	} see Fig. 6/7	0.46	K/W
	per module		0.23	K/W
d _s	Creepage distance on surface		12.7	mm
d _A	Strike distance through air		9.6	mm
a	Maximum allowable acceleration		50	m/s ²

Features

- International standard package JEDEC TO-240 AA
- Direct copper bonded Al₂O₃-ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 148688

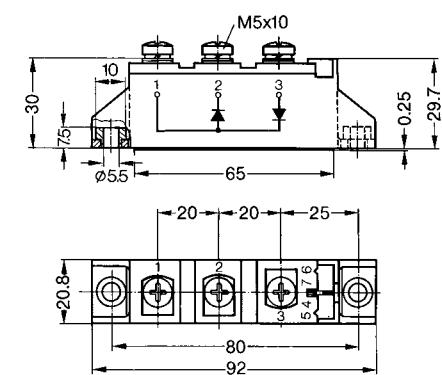
Applications

- Supplies for DC power equipment
- DC supply for PWM inverter
- Field supply for DC motors
- Battery DC power supplies

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

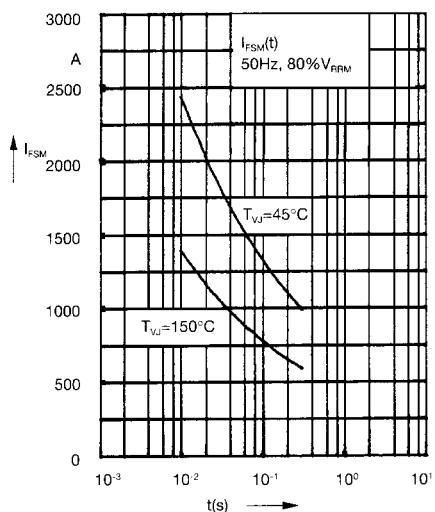


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

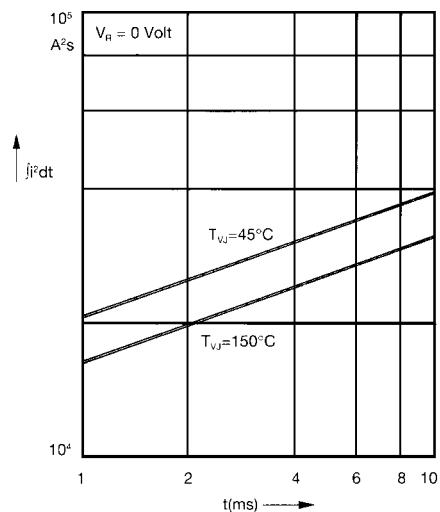


Fig. 2 $\int i^2 dt$ versus time (1-10 ms)

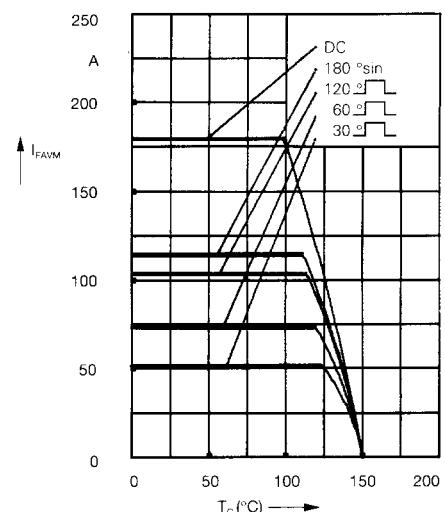


Fig. 2a Maximum forward current at case temperature

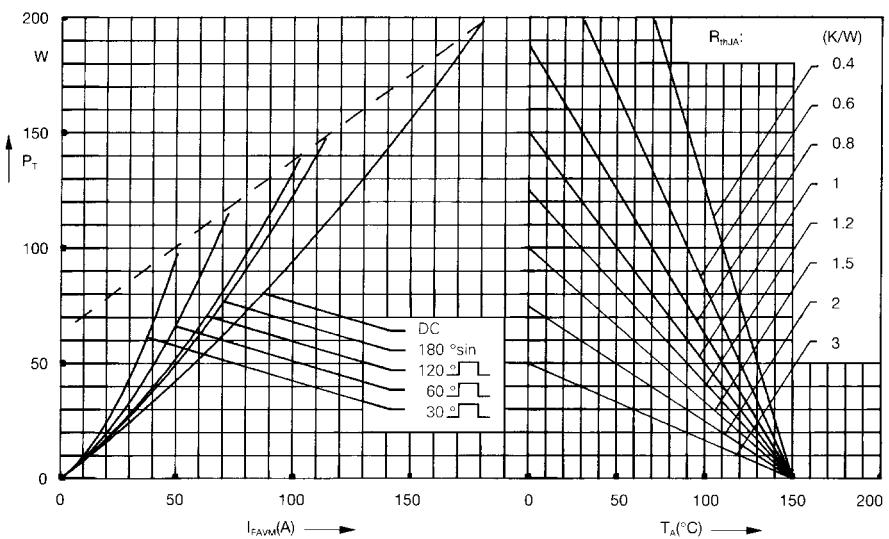


Fig. 3 Power dissipation versus forward current and ambient temperature (per diode)

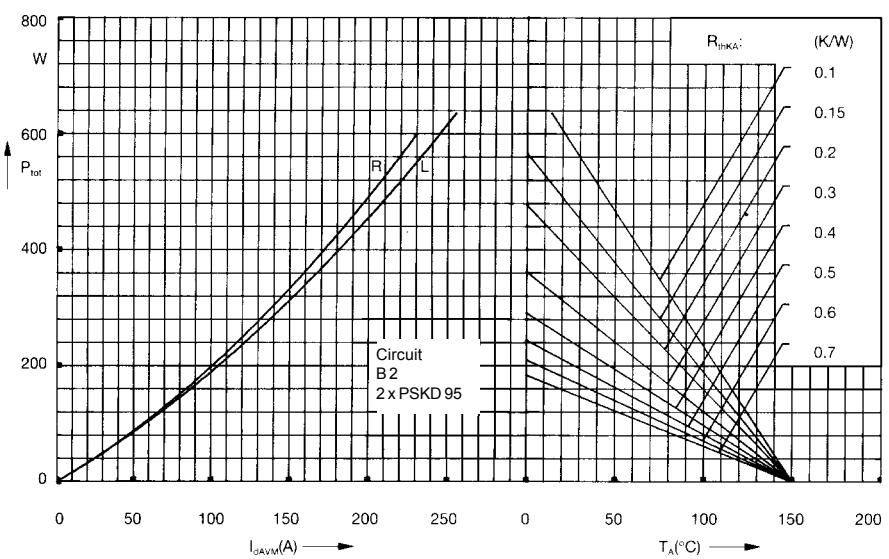


Fig. 4 Single phase rectifier bridge:
Power dissipation versus direct output current and ambient temperature
R = resistive load
L = inductive load

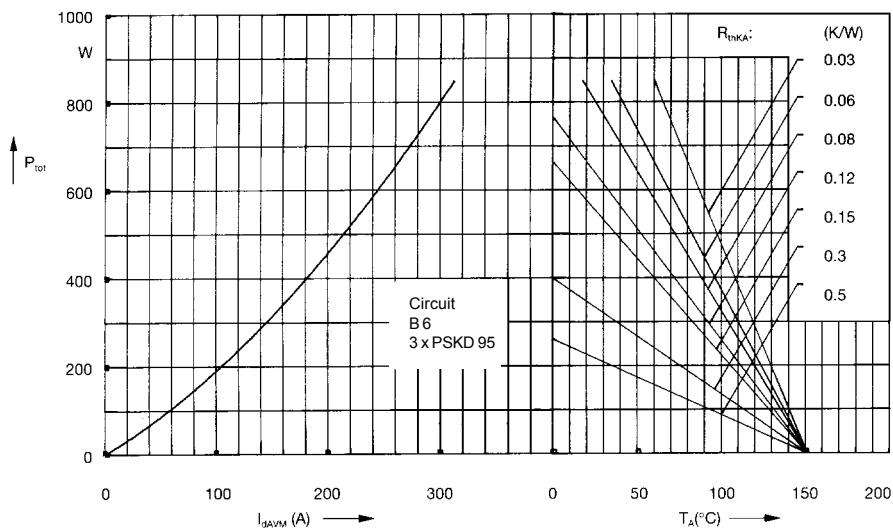


Fig. 5 Three phase rectifier bridge:
Power dissipation versus direct
output current and ambient
temperature

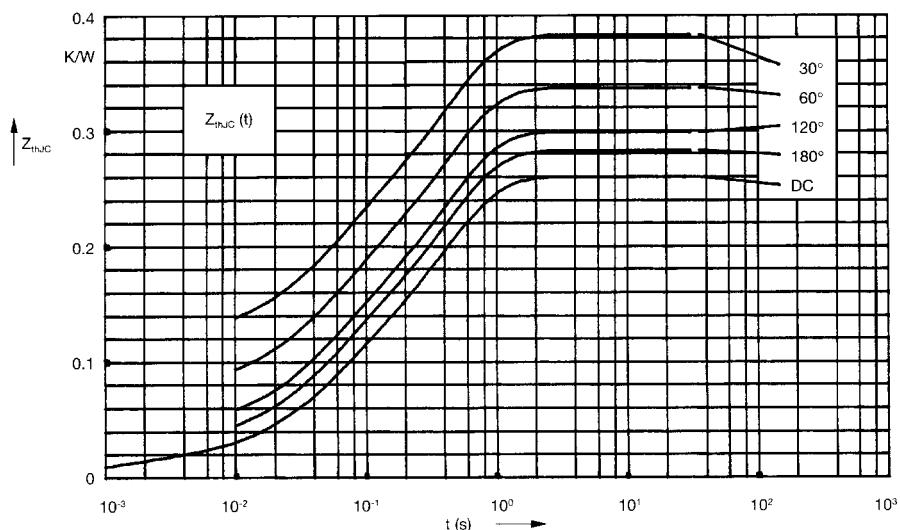


Fig. 6 Transient thermal impedance
junction to case (per diode)

d	R_{thJC} (K/W)
DC	0.26
180°	0.28
120°	0.30
60°	0.34
30°	0.38

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.013	0.0012
2	0.072	0.047
3	0.175	0.394

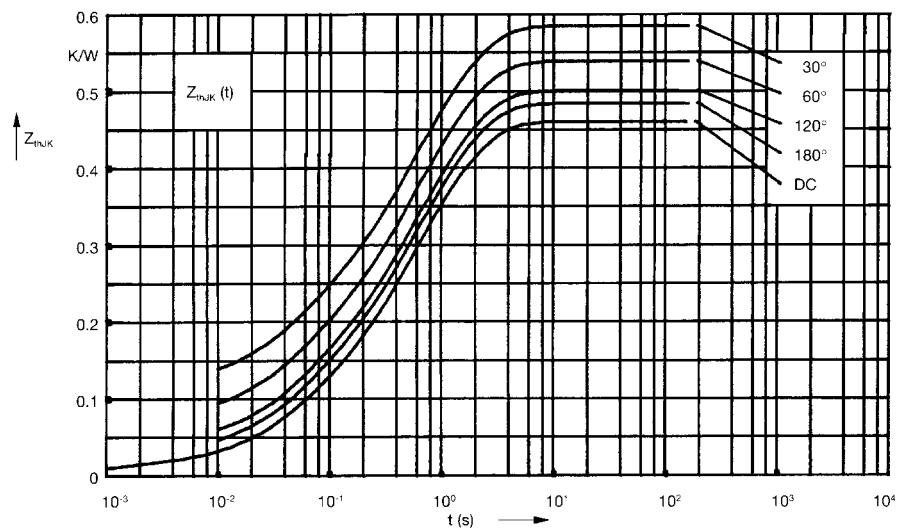


Fig. 7 Transient thermal impedance
junction to heatsink (per diode)

d	R_{thJK} (K/W)
DC	0.46
180°	0.48
120°	0.50
60°	0.54
30°	0.58

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.013	0.0012
2	0.072	0.047
3	0.175	0.394
4	0.2	1.32